

Features

- 100-pin, dual in-line memory module(DIMM)
- Fast data transfer rate: PC2100 and PC2700
- Utilizes 266MT/s or 333MT/s DDR SDRAM components
- 128MB (16 Meg x 32), 256MB (32 Meg x 32), 512MB (64 Meg x 32)
- $V_{DD} = +2.5V$
- 2.5V I/O (SSTL_2 compatible)
- Commands entered on each positive CK edge
- DQS edge-aligned with data for READs; center-aligned with data for WRITEs
- Internal, pipelined double data rate (DDR) architecture; two data accesses per clock cycle
- Bidirectional data strobe (DQS) transmitted/ received with data-*i.e.*, source-synchronous data capture
- Differential clock inputs CK and CK#
- Four internal device banks for concurrent operation
- Programmable burst lengths:2, 4 or 8
- Auto precharge option
- Serial Presence Detect (SPD) with EEPROM
- Programmable READ CAS latency
- Auto Refresh and Self Refresh Modes
- 15.625 μs (128MB), 7.8125 μs (256MB, 512MB)maximum average periodic refresh interval
- Gold edge contacts
- Dual rank

Pin Assignment and Descriptions

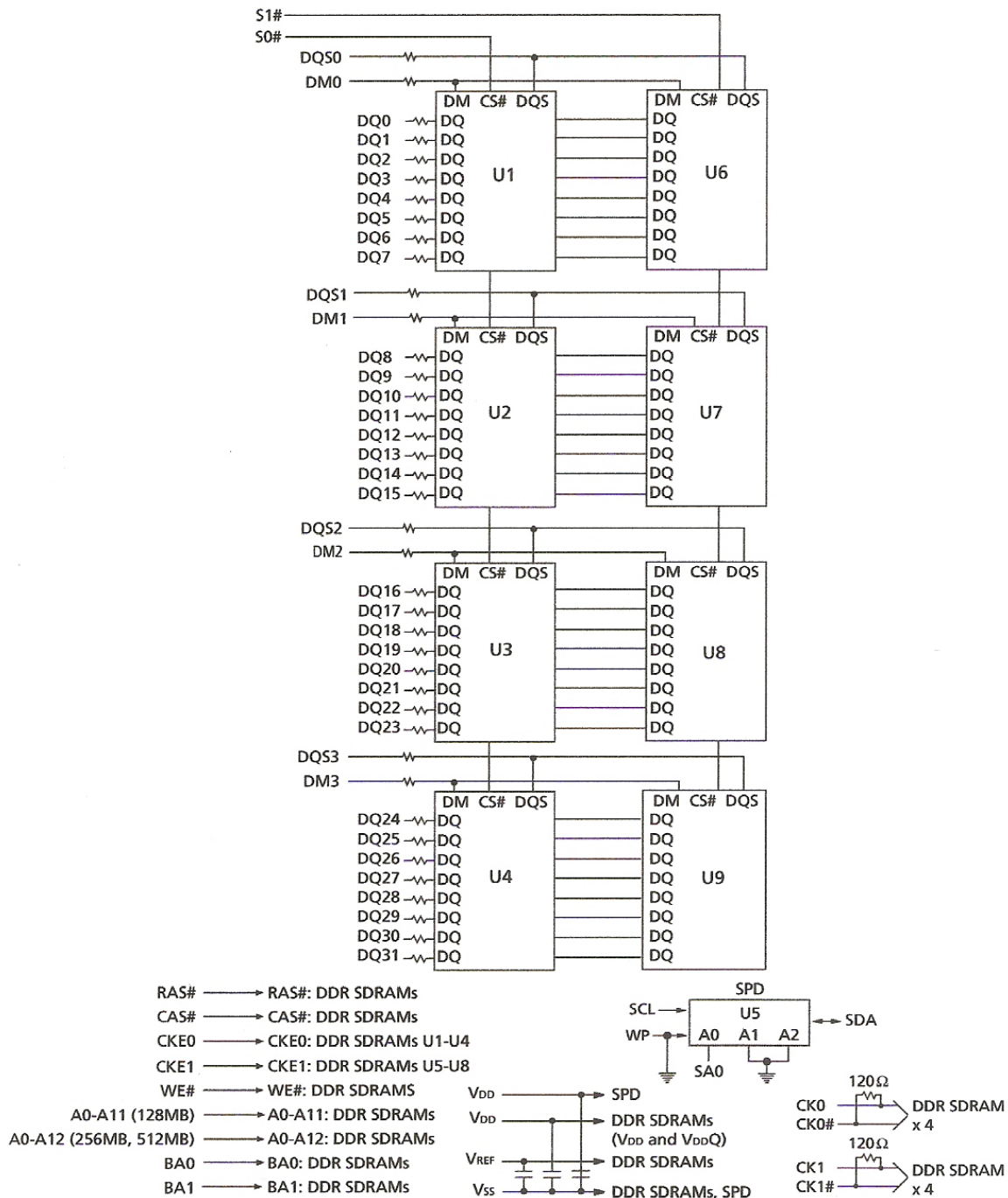
Pin Assignment

100-Pin DIMM Front								100-Pin DIMM Back							
Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol	Pin	Symbol
1	DQ0	14	V _{DD}	26	A5	39	DQ18	51	DQ4	64	V _{DD}	76	A2	89	DQ22
2	V _{SS}	15	DQ11	27	A3	40	DQ19	52	V _{SS}	65	DQ15	77	A0	90	DQ23
3	DQ1	16	V _{SS}	28	A1	41	V _{DD}	53	DQ5	66	V _{SS}	78	BA1	91	V _{DD}
4	DQS0	17	CK0	29	A10	42	DQ24	54	DM0	67	CK1	79	RAS#	92	DQ28
5	V _{DD}	18	CK0#	30	V _{DD}	43	DQ25	55	V _{DD}	68	CK1#	80	V _{DD}	93	DQ29
6	DQ2	19	V _{DD}	31	BA0	44	V _{SS}	56	DQ6	69	V _{DD}	81	CAS#	94	V _{SS}
7	DQ3	20	CKE1	32	WE#	45	DQS3	57	DQ7	70	CKE0	82	S1#	95	DM3
8	V _{DD}	21	NC/A12	33	S0#	46	DQS6	58	V _{DD}	71	A11	83	DNU	96	DQ30
9	DQ8	22	NC	34	DQ16	47	V _{SS}	59	DQ12	72	A8	84	DQ20	97	V _{SS}
10	DQ9	23	A9	35	V _{SS}	48	DQ27	60	DQ13	73	A6	85	V _{SS}	98	DQ31
11	V _{SS}	24	A7	36	DQ17	49	SA0	61	V _{SS}	74	A4	86	DQ21	99	SDA
12	DQS1	25	V _{SS}	37	DQS2	50	V _{REF}	62	DM1	75	V _{SS}	87	DM2	100	SCL
13	DQ10			38	V _{DD}			63	DQ14			88	V _{DD}		

Functional Block

Standard modules use the following DDR SDRAM devices: 16x8 8chips(128MB); 32x8 8chips(256MB); and 64x8 8chips(512MB).

Functional Block Diagram



Parameter Table

Absolute Maximum Ratings

Stresses greater than those listed may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Voltage on VDD Supply Relative to VSS	-1V to +3.6V
Voltage on VREF and Inputs Relative to VSS	-1V to +3.6V
Voltage on I/O Pins Relative to VSS	-0.5V to VDD +0.5V
Operating Temperature,	
T _A (commercial - ambient)	0°C to +70°C
T _A (industrial - ambient)	-40°C to +85°C
Storage Temperature (plastic)	-55°C to +150°C
Short Circuit Output Current	50mA

DC Electrical Characteristics and Operating Conditions

Notes: 1-5, 14, 48; notes appear on pages 23-27; 0°C ≤ T_A ≤ +70°C

Parameter/Condition	Symbol	Min	Max	Units	
Supply Voltage	VDD	2.3	2.7	V	
I/O Supply Voltage	VDD	2.3	2.7	V	
I/O Reference Voltage	VREF	0.49xVDD	0.51xVDD	V	
I/O Termination Voltage (system)	VTT	VREF - .04	VREF+0.04	V	
Input High (Logic 1) Voltage	V _{IH} (DC)	VREF+0.15	VDD + 0.3	V	
Input Low (Logic 0) Voltage	V _{IL} (DC)	-0.3	VREF -0.15	V	
INPUT LEAKAGE CURRENT Any input 0V ≤ V _{IN} ≤ VDD, VREF pin 0V ≤ V _{IN} ≤ 1.35V (All other pins not under test = 0V)	Command/ Address, RAS#, CAS#, WE#	I _I	-16	16	μA
	CKE0, CKE1, S0#, S1# CK, CK#		-8	8	
	DM		-4	4	
	OUTPUT LEAKAGE CURRENT (DQs are disabled; 0V ≤ V _{OUT} ≤ VDD)		DQ, DQS	I _{OZ}	
OUTPUT LEVELS High Current (V _{OUT} = VDD-0.373V, minimum VREF, minimum VTT) Low Current (V _{OUT} = 0.373V, maximum VREF, maximum VTT)	I _{OH}	-16.8	-	mA	
	I _{OL}	16.8	-	mA	

AC Input Operating Conditions

Notes: 1-5, 14, 48, 49; notes appear on pages 23-27; 0°C ≤ T_A ≤ +70°C; VDD = +2.5V ±0.2V

Parameter/Condition	Symbol	Min	Max	Units
Input High (Logic 1) Voltage	V _{IH} (AC)	VREF + 0.310	-	V
Input Low (Logic 0) Voltage	V _{IL} (AC)	-	VREF - 0.310	V
I/O Reference Voltage	VREF (AC)	0.49 × VDD	0.51 × VDD	V

Module Dimension

All dimensions are in inches (millimeters); $\frac{MAX}{MIN}$ or typical where noted.

100-Pin DIMM Dimensions

